

P-Channel Enhancement Mode Power MOSFET

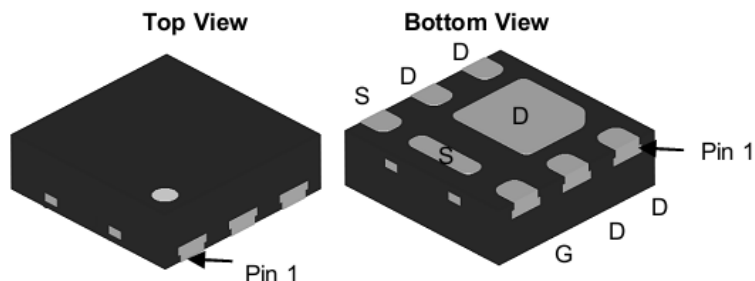
Features

$V_{DS} = -30V$,
 $I_D = -12A$
 $R_{DS(ON)} @ V_{GS} = -10V$, TYP $26m\Omega$
 $R_{DS(ON)} @ V_{GS} = -4.5V$, TYP $35m\Omega$

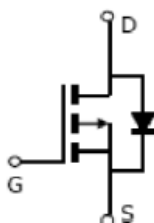
General Description

- DC-DC Converters
- Power Management Functions
- Battery Management Application

Pin Configurations



DFN2*2-6L
 MARKING:4435



Absolute Maximum Ratings @ $T_A=25^\circ C$ unless otherwise noted

Parameter		Symbol	Ratings	Unit
Drain-Source Voltage		V_{DSS}	-30	V
Gate-Source Voltage		V_{GSS}	± 20	V
Drain Current (Continuous) *AC	$T_C=25^\circ C$	I_D	-12	A
	$T_C=70^\circ C$		-12	
Drain Current (Pulse) *B		I_{DM}	-35	A
Power Dissipation	$T_C=25^\circ C$	P_D	19	W
Operating Temperature/ Storage Temperature		T_J/T_{STG}	-55~150	$^\circ C$

Thermal Resistance Ratings

Parameter		Symbol	Maximum	Unit
Maximum Junction-to-Ambient	$t \leq 5s$	R_{thJA}	36	$^\circ C/W$
Thermal Resistance, Junction to Case	Steady State	R_{thJC}	6.5	

Electrical Characteristics @T_A=25°C unless otherwise noted

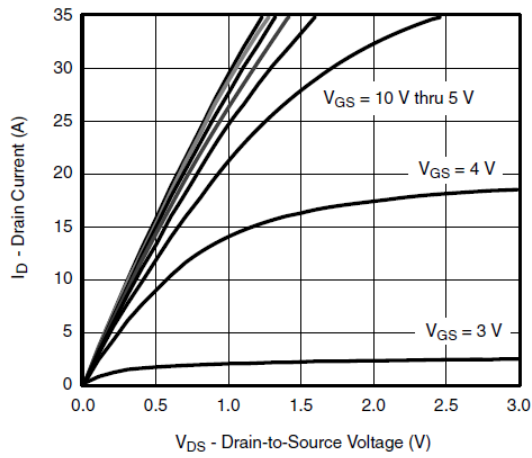
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-30	--	--	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -30V, V _{GS} = 0V	--	--	-1	μA
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _{DS} = -250μA	-1	-1.45	-3	V
Gate Leakage Current	I _{GSS}	V _{GS} = ± 20V, V _{DS} =0V	--	--	±100	μA
Drain-Source On-state Resistance	R _{DS(on)}	V _{GS} = -10V, I _D = -10A	--	26	34	mΩ
	R _{DS(on)}	V _{GS} = -4.5V, I _D = -7A	--	35	45.5	mΩ
Diode Forward Voltage	V _{SD}	I _{SD} = -1A , V _{GS} =0V	--	-0.77	-1.2	V
Diode Forward Current *AC	I _S	T _C =25°C	--	--	-12	A
Switching						
Total Gate Charge	Q _g	V _D S = - 15 V, V _G S = - 4.5 V, I _D = - 7.9 A	--	10	--	nC
Gate-Source Charge	Q _{gs}		--	3	--	nC
Gate-Drain Charge	Q _{gd}		--	4.5	--	nC
Turn-on Delay Time	t _{d (on)}	V _D D = - 15 V, R _L = 2.4Ω I _D = - 6.3 A, V _G EN = - 4.5V, R _g = 1Ω	--	40	--	ns
Turn-on Rise Time	t _r		--	110	--	ns
Turn-off Delay Time	t _{d(off)}		--	25	--	ns
Turn-Off Fall Time	t _f		--	12	--	ns
Dynamic						
Input Capacitance	C _{iSS}	V _D S= -15V,V _G S=0V, f=1.0MHz	--	950	--	pF
Output Capacitance	C _{oSS}		--	150	--	pF
Reverse Transfer Capacitance	C _{rSS}		--	120	--	pF

A: The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design.

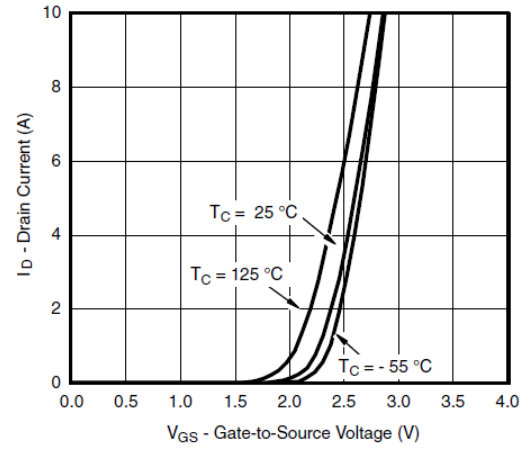
B: Repetitive rating, pulse width limited by junction temperature.

C: The current rating is based on the t_≤ 10s junction to ambient thermal resistance rating, Package limited 12A.

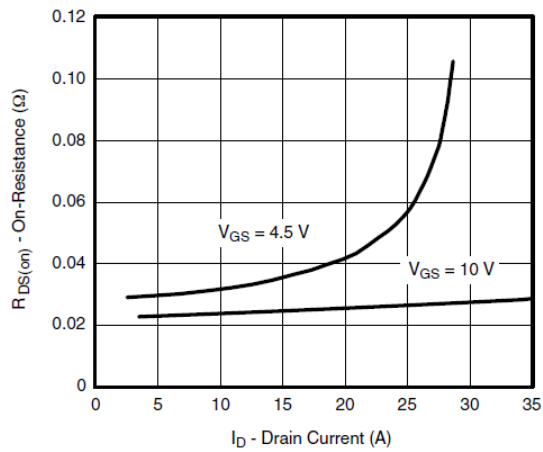
Typical Performance Characteristics (T_J = 25 °C, unless otherwise noted)



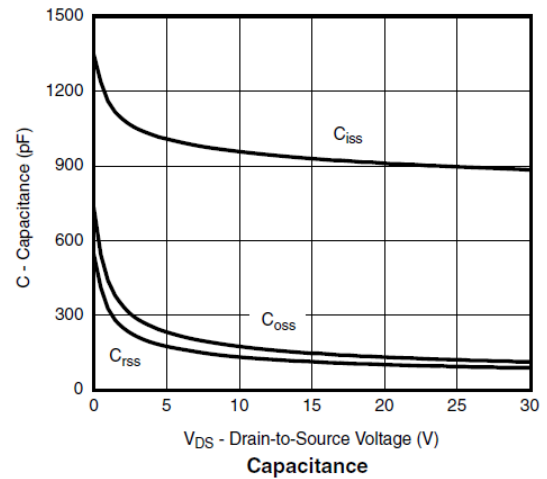
Output Characteristics



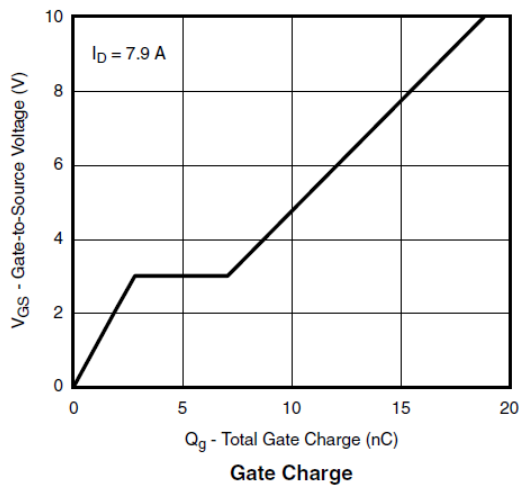
Transfer Characteristics



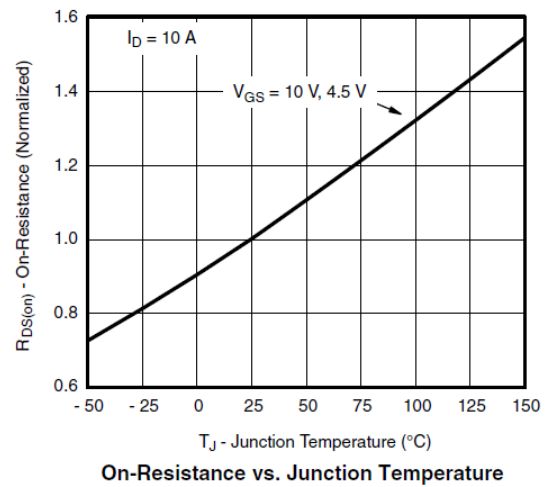
On-Resistance vs. Drain Current and Gate Voltage



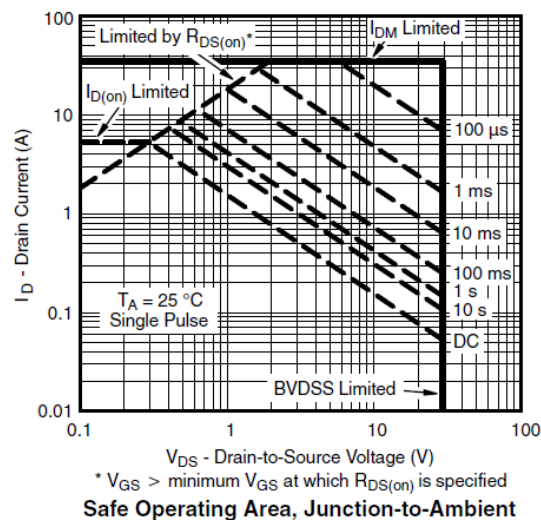
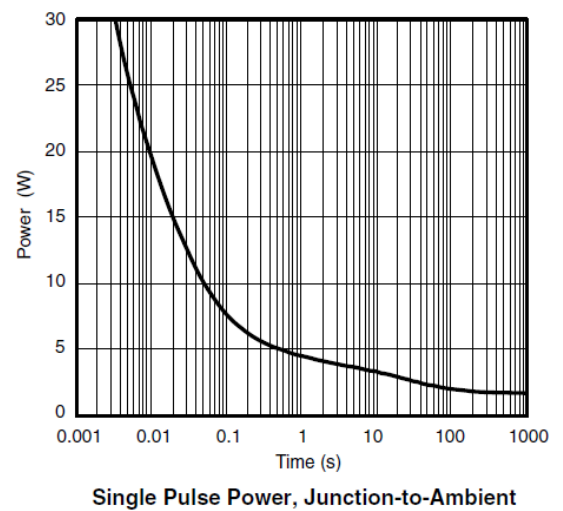
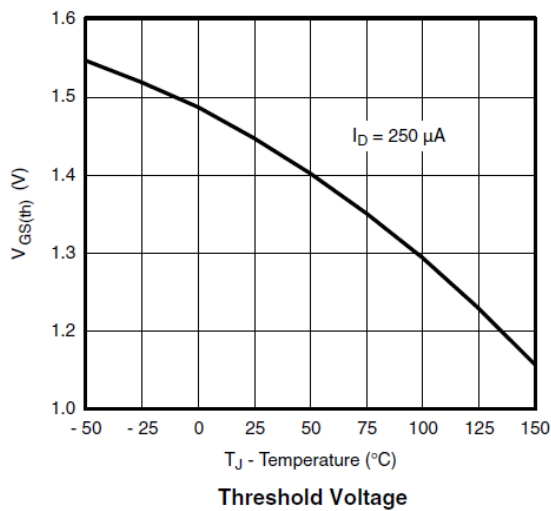
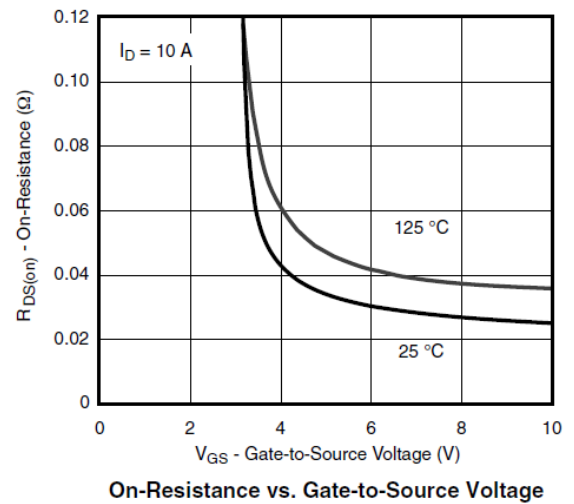
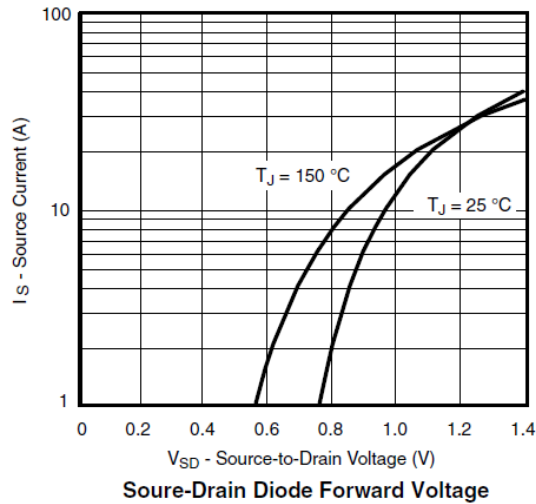
Capacitance

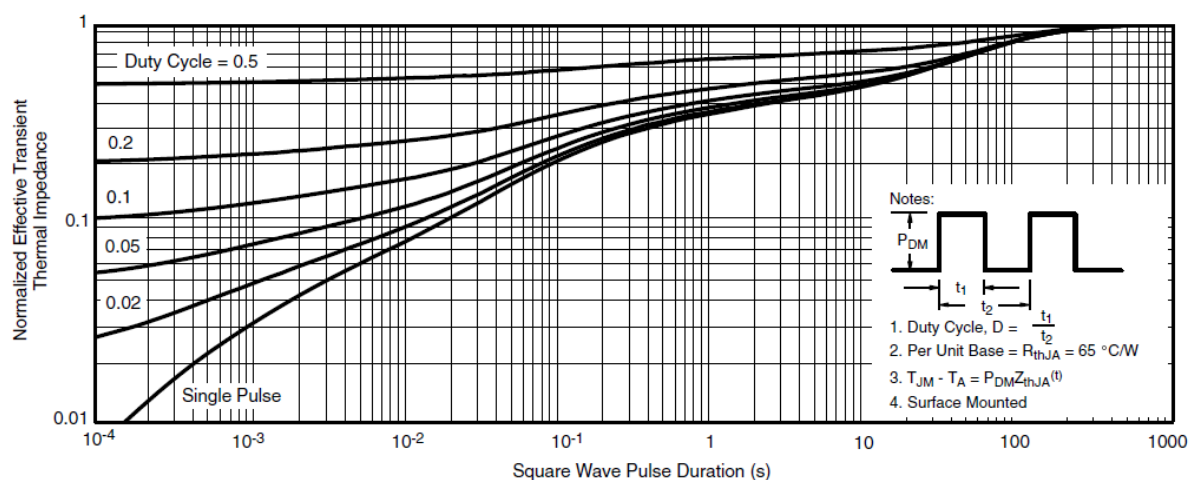


Gate Charge

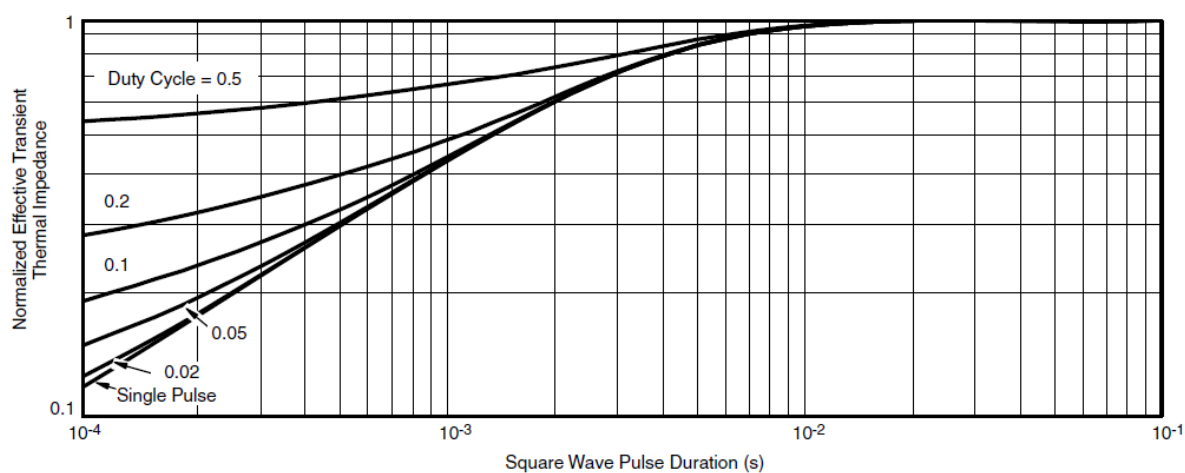


On-Resistance vs. Junction Temperature





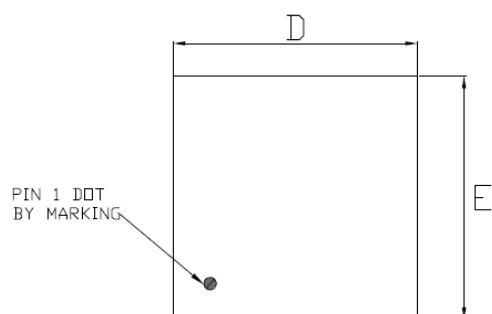
Normalized Thermal Transient Impedance, Junction-to-Ambient



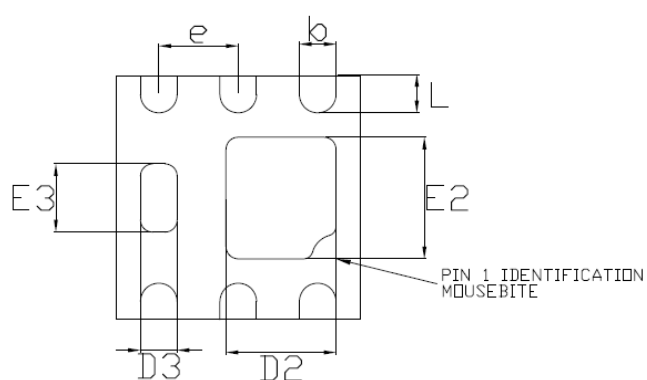
Normalized Thermal Transient Impedance, Junction-to-Case

Package Information

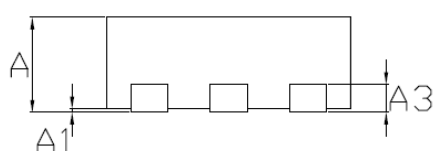
DFN2X2-6 Package Out Line A



TOP VIEW



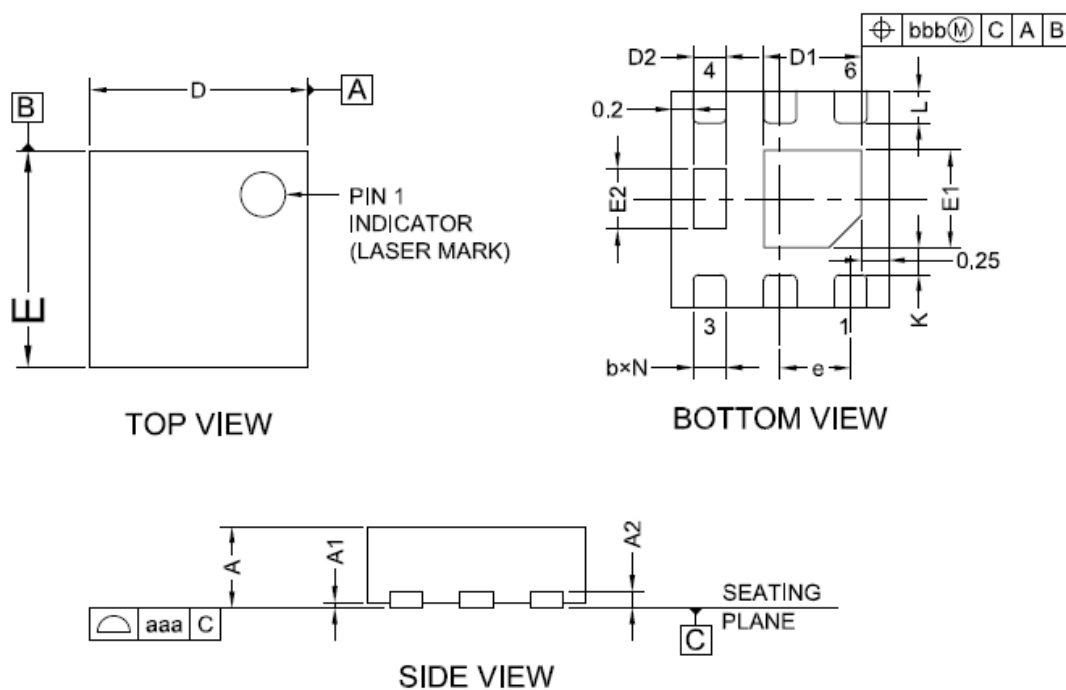
BOTTOM VIEW



SIDE VIEW

COMMON DIMENSIONS(MM)			
PKG.	WVERY VERY THIN		
REF.	MIN.	NOM.	MAX.
A	0.70	0.75	0.80
A1	0.00	-	0.05
A3	0.20 REF.		
D	1.95	2.00	2.05
E	1.95	2.00	2.05
D2	0.85	0.90	0.95
E2	0.95	1.00	1.05
D3	0.25	0.30	0.35
E3	0.51	0.56	0.61
b	0.25	0.30	0.35
L	0.25	0.30	0.35
e	0.65 BSC		

DFN2X2-6 Package Out Line B



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	TYP	MAX
A	0.50	0.55	0.60
A1	0.00	0.02	0.05
A2	0.152REF.		
b	0.25	0.30	0.35
D	1.95	2.00	2.05
D1	0.80	0.90	1.00
D2	0.25	0.30	0.35
E	1.95	2.00	2.05
E1	0.80	0.90	1.00
E2	0.46	0.56	0.66
e	0.65BSC		
L	0.25	0.30	0.35
J	0.40BSC		
K	0.20MIN		
N	6		
aaa	0.08		
bbb	0.10		